

Patent number Tokko No.51-45234 "Hall Element and Manufacturing method of Hall Element"

[Claim]

1. Hall element consisting of a first magnetic material, a vapor-deposited semiconductor thin film bonded to one surface of the first magnetic material with an adhesive and separated from the vapor deposition substrate, and a second magnetic material bonded to the top surface of the vapor-deposited semiconductor thin film with an adhesive.

2. Manufacturing method of Hall element, comprising forming a semiconductor thin film by vapor deposition on a smooth surface substrate; bonding a first magnetic material onto the vapor deposited semiconductor thin film with an adhesive; thereafter, removing the vapor deposition substrate from the vapor deposition thin film; and bonding a second magnetic material to the surface of the vapor deposited semiconductor thin film from which the vapor deposition substrate has been removed with an adhesive .